



<b>Session Title:</b>	<b>[MB1] Power Device I</b>
<b>Session Date:</b>	<b>November 20 (Mon.), 2023</b>
<b>Session Time:</b>	<b>13:00-14:45</b>
<b>Session Room:</b>	<b>Room B (Grand Ballroom 1, 2F)</b>
<b>Session Chair:</b>	<b>Prof. Ogyun Seok (Kumoh Nat'l Inst. of Tech., Korea)</b>

**[MB1-1] [Invited] 13:00-13:20**

**Low Turn-On Voltage Silicon Carbide Diode**

Kevin Kyuheon Cho, Changjoon Park, Yeonjeong Kim, and Kyeongseok Park (onsemi, Korea)

**[MB1-2] [Invited] 13:20-13:40**

**4H-SiC Epitaxial Growth Technology for Large Area Substrate**

Han Seok Seo, Im Gyu Yeo, Tai Hee Eun, and Myong Chuel Chun (RIST, Korea)

**[MB1-3] 13:40-14:00**

**Design of A 1.2 kV SiC MOSFET with Buried Oxide for Improved Gate Charge Characteristics**

Hyowon Yoon, Chaeyun Kim, Yeongeun Park, Sangyeob Kim, Jinhun Kim, Sumin Park, Dusan Baek, and Ogyun Seok (Kumoh Nat'l Inst. of Tech., Korea)

**[MB1-4] [Plenary] 14:00-14:45**

**On the Origin of Gate Oscillation of Power Devices**

Hyemin Kang (KENTECH, Korea)